

VUSN002R26ANA

Datasheet

260mΩ, 20V, N-Channel Power MOSFET

VUSN002R26ANA

General Description

V _{(BR)DSS}	R _{DS(ON)_max}	I_D	
	260mΩ@4.5V		
20V	360mΩ@2.5V	0.75A	
	590mΩ@1.8V		

Symbol

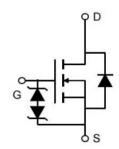
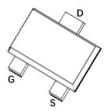


Figure 1 Symbol of VUSN002R26ANA

Features

- Lead Free Product is Acquired
- N-Channel Switch with Low R_{DS(on)}
- Surface Mount Package
- Operated at Low Logic Level Gate Drive

Package Type



Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift
- Battery Management for Ultra Small Portable

SOT-723

Figure 2 Package Type of VUSN002R26ANA

Ordering Information

Product Name	Package
VUSN002R26ANA	SOT-723



VUSN002R26ANA

Absolute Maximum Ratings (T_A = 25 °C, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current Note1	I_D	0.75	A
Pulsed Drain Current (tp=10us)	I_{DM}	1.8	A
Total Power Dissipation Note1	P_{D}	0.15	W
Junction Temperature	$T_{\rm J}$	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	$T_{ m L}$	260	°C

Thermal Resistance

Parameter	Symbol	Min	Тур	Max	Unit
Thermal Resistance, Junction-to-Ambient Note1	$R_{ heta JA}$		833		°C/W



VUSN002R26ANA

Electrical Characteristics (T_A= 25 °C, unless otherwise specified)

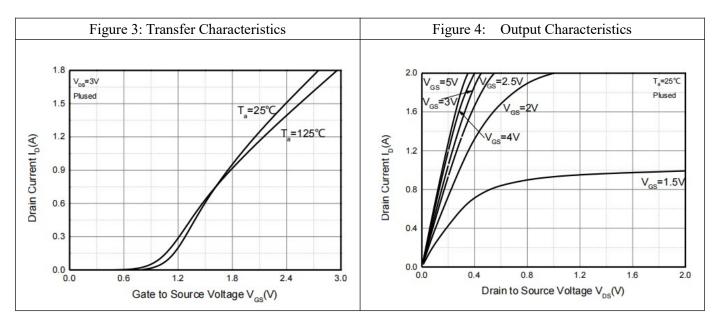
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Statistic Characteristics							
Drain-Source Breakdown Voltage	$\mathrm{BV}_{\mathrm{DSS}}$	$V_{GS}=0V, I_{D}=250uA$	20			V	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20V, V_{GS} =0V			1	uA	
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			±20	uA	
Gate Threshold Voltage Note2	$V_{\text{GS(th)}}$	$V_{DS}=V_{GS}$, $I_D=250uA$	0.35	0.75	1.1	V	
		V_{GS} =4.5V, I_D = 0.65A		190	260		
Static Drain-Source On-Resistance ^{Note2}	R _{DS(ON)}	V_{GS} = 2.5V, I_D = 0.55A		260	360	$m\Omega$	
		V_{GS} = 1.8V, I_{D} = 0.45A		390	590		
Forward tranconductance	g_{FS}	V_{DS} = 10V, I_{D} = 0.8A		1.6		S	
Dynamic Characteristics Note4							
Input Capacitance	C_{ISS}	$V_{DS}=16V$		79	120	pF	
Output Capacitance	Coss	$V_{GS}=0V$		13	20	pF	
Reverse Transfer Capacitance	C _{RSS}	f=1MHz		9	15	pF	
Switching Parameters Note4							
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V$		6.7			
Turn-on Rise Time	$t_{\rm r}$	$V_{GS}=4.5V$		4.8			
Turn-off Delay Time	$t_{ m d(off)}$	$I_D=0.5A$		17.3		ns	
Turn-off Fall Time	t_{f}	$R_G=10\Omega$		7.4			
Diode Characteristics							
Diode Forward Voltage Note3	V_{SD}	$V_{GS}=0V, I_{S}=0.15A$			1.2	V	

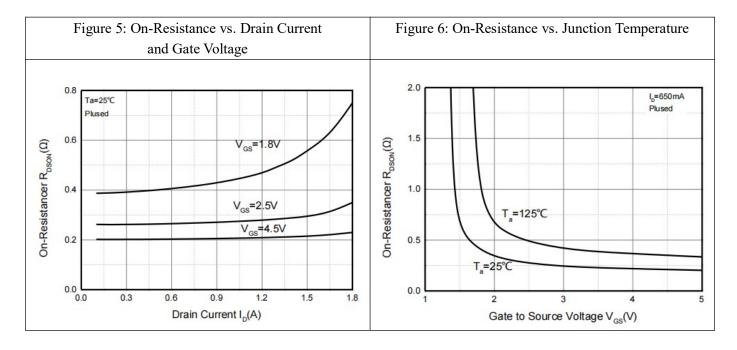
Notes:

- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test: Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.

VUSN002R26ANA

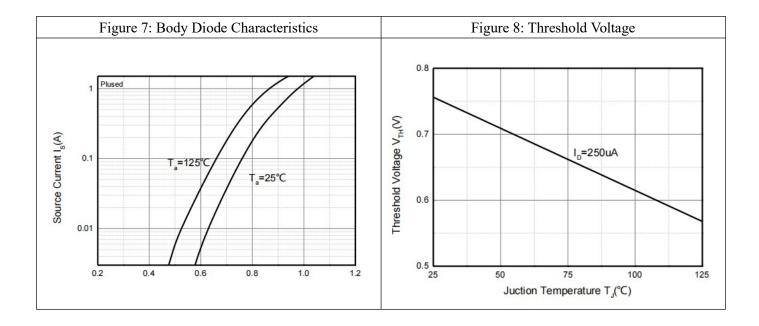
Typical Performance Characteristics







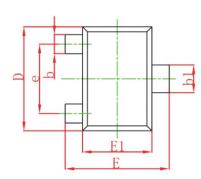
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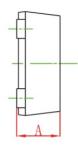


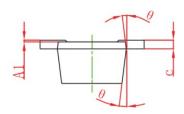


Mechanical Dimensions:

SOT-723 Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
Α	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
С	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
е	0.800TYP.		0.03	1TYP.
θ	7° REF.		7° F	REF.



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VUSN002R26ANA

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